

MA2C856

Silicon epitaxial planar type

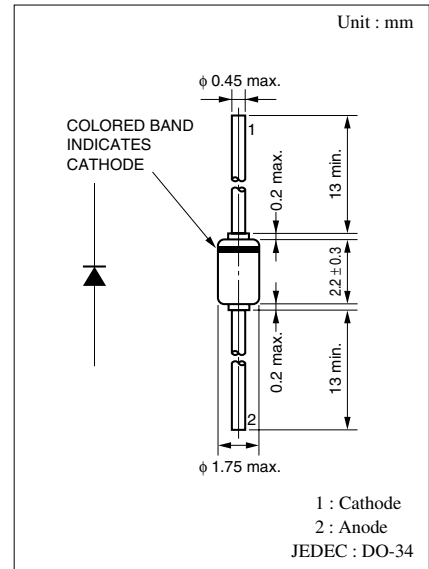
For band switching

■ Features

- Extra-small DHD envelope, allowing to insert into a 5 mm pitch hole
- Less voltage dependence of the terminal capacitance C_t
- Low forward dynamic resistance r_f
- Optimum for a band switching of a tuner

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +100	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)*	I_R	$V_R = 33\text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$			1	V
Terminal capacitance	C_t	$V_R = 15\text{ V}, f = 1\text{ MHz}$			2	pF
Forward dynamic resistance	r_f	$I_F = 3\text{ mA}, f = 100\text{ MHz}$			0.85	Ω

Note) 1. Rated input/output frequency: 100 MHz

2. *: Measurement with the beam shielded

■ Cathode Indication

Type No.	MA2C856
Color	Yellow

